Supplementary Information

Screening limited switching performance of multilayer 2D semiconductor FETs: the case for SnS

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Anisotropic Hall mobility of SnS multilayer devices

Anisotropic conductance was observed in SnS nanoflake van der Pauw devices, suggesting the holes have anisotropic transport mobility. The direction dependent Hall mobility for the 60 nm thick SnS device discussed in Figure 2 and 3 of the main manuscript is analyzed and displayed in Figure S1.

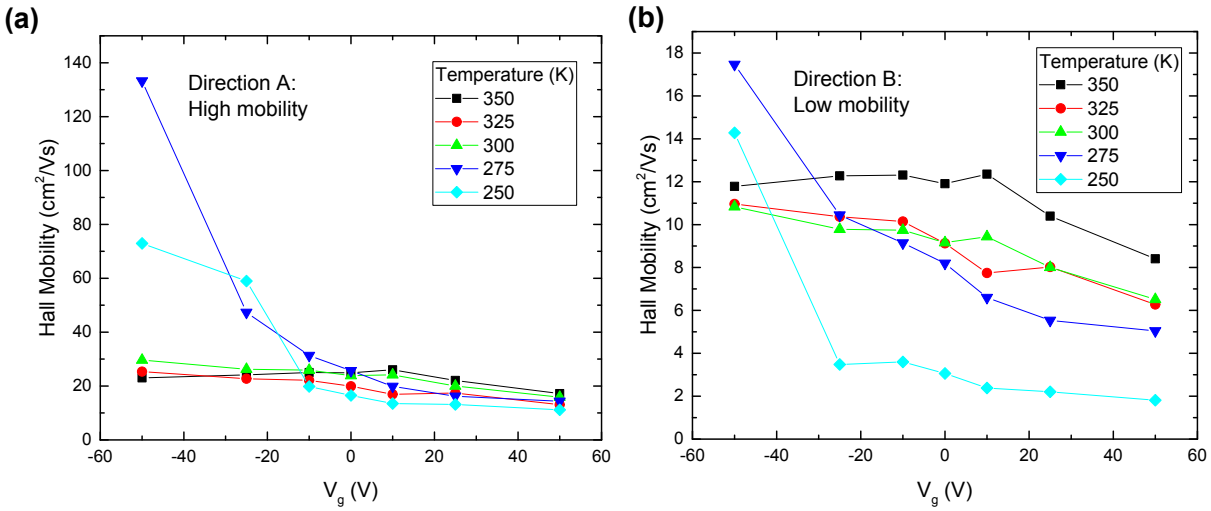

Fig. S1. Hall mobility for holes in a 60 nm thick SnS FET device along the high mobility or A-direction (a), and the low mobility or B-direction (b) *vs.* the backgate voltage at different temperatures.